

Schottky barrier diode

Applications

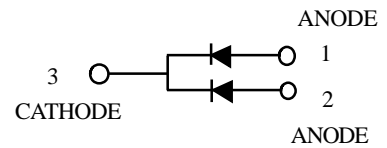
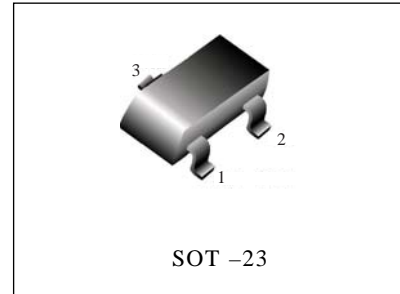
Low power rectification

Features

- 1) Small surface mounting type.
- 2) Low V_F . ($V_F=0.45V$ Typ. at 100mA)
- 3) High reliability.
- 4) We declare that material of product compliance with ROHS requirements.

Construction

Silicon epitaxial planar



DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
FDR425	D3L	3000/Tape&Reel

Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_o	0.1	A
Peak forward surge current [□]	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ C$
Storage temperature	T_{stg}	-40~+150	$^\circ C$

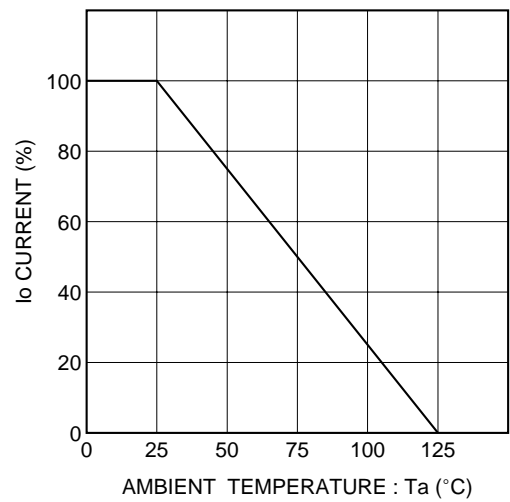
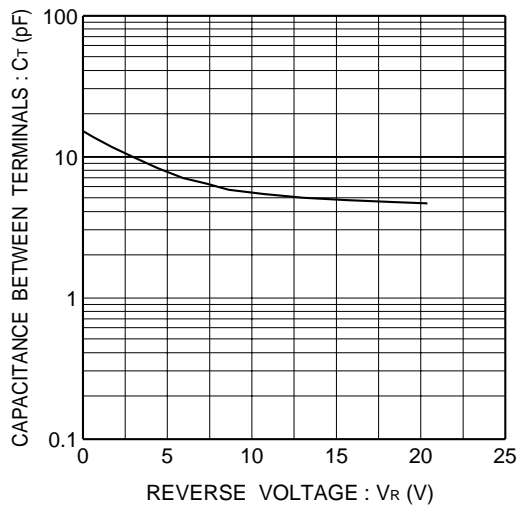
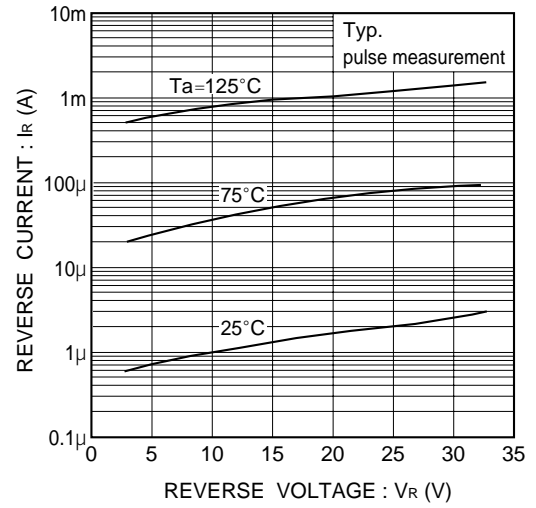
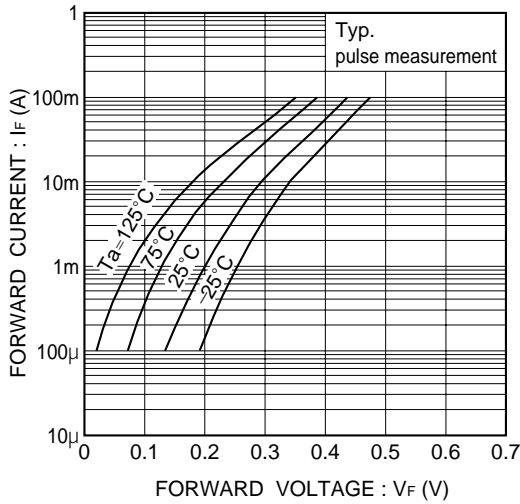
□ 60Hz for 1

Electrical characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	—	—	0.55	V	$I_F=100mA$
Forward voltage	V_{F2}	—	—	0.34	V	$I_F=10mA$
Reverse current	I_R	—	—	30	μA	$V_R=10V$
Capacitance between terminals	C_T	—	6.0	—	pF	$V_R=10V, f=1MHz$

Note) ESD sensitive product handling required.

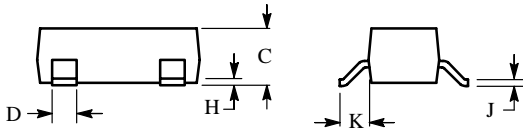
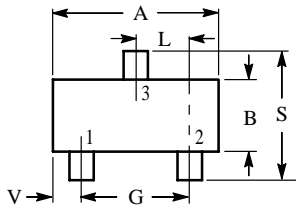
Electrical characteristic curves (Ta = 25°C)



SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1 BASE
 2 EMITTER
 3 COLLECTOR

